

Substitute for form 1449/PTO

**INFORMATION DISCLOSURE
STATEMENT BY APPLICANT**

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Application Number	10/524,809
Filing Date	02/15/2005
Inventor(s)	James S. Im
Art Unit	2895
Examiner Name	Fernando L. Toledo
Attorney Docket Number	070050.2721

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Exam Initial	No.	Document No.	Publication Date	Applicant(s)
	1.	4514895	5/7/1985	Nishimura, Tadashi
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	6.	5466908	11/14/1995	Hosoya, Kimio ; Teruya, Yoshihiro ; Kobayashi, Yasushi
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	12.	5710050	1/20/1998	Makita, Naoki ; Miyamoto, Tadayoshi
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	14.	6093934	7/25/2000	Yamazaki, Shunpei ; Teramoto, Satoshi ; Koyama, Jun ; Ogata, Yasushi ; Hayakawa, Masahiko ; Osame, Mitsuaki ; Ohtani, Hisashi ; Hamatani, Toshiji
	15.	6117301	9/12/2000	Freudenberger, Renate ; Zielonka, Andreas
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	18.	6255146	7/3/2001	Shimizu, Satoshi ; Ueno, Shuichi ; Maeda, Shigenobu ; Ipposhi, Takashi
	19.	6274488	8/14/2001	Talwar, Somit ; Wang, Yun
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	21.	6348990	2/19/2002	Igasaki, Yasunori ; Yoshida, Narihiro ; Toyoda, Haruyoshi ; Hara, Tsutomu
	22.	6353218	3/5/2002	Yamazaki, Shunpei ; Tanaka, Koichiro
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	24.	6388386	5/14/2002	Kunii, Masafumi ; Takatoku, Makoto ; Mano, Michio

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	49.	6577380	6/10/2003	Sposili, Robert S. ; Farmiga, Nestor O. ; Jain, Kanti

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	52.	6635932	10/21/2003	Grigoropoulos, Costas P. ; Hatano, Mutsuko ; Lee, Ming Hong ; Moon, Seung Jae
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	62.	6961117	11/1/2005	Im, James S.
	63.	7091411	8/15/2006	Falk, Fritz ; Andrae, Gudrun

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	65.	7217605	5/15/2007	Kawasaki, Ritsuko ; Nakajima, Setsuo
	66.	7259081	8/21/2007	Im, James S.
	67.	7297982	11/20/2007	Suzuki, Kenkichi ; Nagata, Tetsuya ; Takahashi, Michiko ; Saito, Masakazu ; Ogino, Toshio ; Miyano, Masanobu
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	73.	20020119609	8/29/2002	Hatano, Mutsuko ; Yamaguchi, Shinya ; Kimura, Yoshinobu ; Park, Seong Kee
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	79.	20030068836	4/10/2003	Hongo, Mikio ; Uto, Sachio ; Nomoto, Mineo ; Nakata, Toshihiko ; Hatano, Mutsuko ; Yamaguchi, Shinya ; Ohkura, Makoto
	80.	20030119286	6/26/2003	Im, James, S. ; Sposili, Robert, S. ; Crowder, Mark, A.
	81.	20030148565	8/7/2003	Yamanaka, Hideo
	82.	20030194613	10/16/2003	Voutsas, Apostolos, T. ; Crowder, Mark, A. ; Mitiani, Yasuhiro
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	87.	20040222187	11/11/2004	Lin, Kun Chih
	88.	20040224487	11/11/2004	Yang, Myoung Su
	89.	20050059265	3/17/2005	Im, James

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	93.	20050202654	9/15/2005	Im, James
	94.	20060030164	2/9/2006	Im, James
	95.	20060102901	5/18/2006	Im, James ; van der Wilt, Paul
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	99.	20070007242	1/11/2007	Im, James
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	101.	20070032096	2/8/2007	Im, James, S.
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	103.	20070111349	5/17/2007	Im, James

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Application Number	10/524,809
Filing Date	02/15/2005
Inventor(s)	James S. Im
Art Unit	2895
Examiner Name	Fernando L. Toledo
Attorney Docket Number	070050.2721

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